

CLAIMS

1. A hot plate for a semiconductor producing/examining device, comprising a resistance heating element formed on a surface of
5 a ceramic substrate or inside the ceramic substrate,
wherein the glossiness of the heating face of said ceramic substrate is 1.5 % or more.

2. The hot plate for a semiconductor producing/examining device according to claim 1,
10 wherein said ceramic substrate contains 0.5 to 10 weight % of oxygen.

3. The hot plate for a semiconductor producing/examining device according to claim 1 or 2,
15 wherein said ceramic substrate is subjected to an annealing treatment.

4. The hot plate for a semiconductor producing/examining device according to any of claims 1 to 3,
20 wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

Sub A2
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Add A3